



WBFBP-03B Plastic-Encapsulate Transistors

DS54NND03

SCHOTTKY DIODE

DESCRIPTION

Epitaxial planar Silicon diode

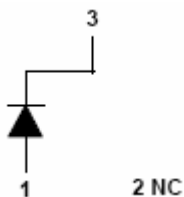
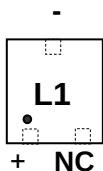
FEATURES

- Ultra-Small Surface Mount Package
- Low Forward Voltage Drop
- Fast Switching
- PN Junction Guard Ring for Transient and ESD Protection
- Available in Lead Free Version

APPLICATION

Ultra high speed switching
For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

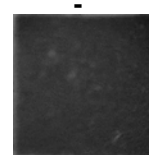
MARKING: L1



WBFBP-03B

(1.2×1.2×0.5)
unit: mm

TOP



1. ANODE

2. NC

3. CATHODE

BACK



Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	30	V
Working Peak Reverse Voltage	V _{RWM}		
DC Blocking Voltage	V _R		
Forward Continuous Current (Note 1)	I _{FM}	200	mA
Repetitive Peak Forward Current	I _{FRM}	300	mA
Forward Surge Current @ t < 1.0s	I _{FSM}	600	mA
Power Dissipation (Note 1)	P _d	150	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	833	°C/W
Junction temperature	T _J	125	°C
Storage temperature range	T _{STG}	-65-125	°C

Notes:1. Device mounted on FR-4 PC board with recommended pad layout

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	30		V
Reverse voltage leakage current	I_R	$V_R = 25V$		2	μA
Forward voltage	V_F	$I_F = 0.1mA$ $I_F = 1mA$ $I_F = 10mA$ $I_F = 30mA$ $I_F = 100mA$		240 320 400 500 1000	mV
Total capacitance	C_T	$V_R = 1V, f = 1MHz$		10	pF
Reverse recovery time	t_{rr}	$I_F = 10mA, I_R = 10mA \sim 1mA$ $R_L = 100\Omega$		5	nS

Typical Characteristics

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